

N-channel Enhancement Mode Power MOSFET

Features

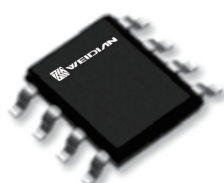
- Advanced Trench Technology
- Provide Excellent RDS(ON) and Low Gate Charge
- Lead free product is acquired
- 100% UIS TESTED!, 100% Rg TESTED!

Product Summary

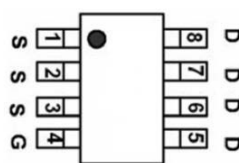
Parameters	Value	Unit
V_{DSS}	60	V
$V_{GS(th)_{Typ}}$	1.6	V
$I_D(@V_{GS}=10V)$	50	A
$R_{DS(ON)_{Typ}}(@V_{GS}=10V)$	15	mΩ
$R_{DS(ON)_{Typ}}(@V_{GS}=4.5V)$	21	mΩ

Applications

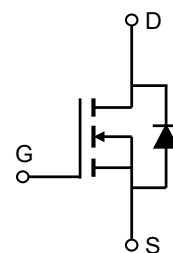
- Load Switch
- PWM Application
- Power management



SOP8 Top View



Marking



Schematic Diagram

Device	Marking	Package	Packing	Reel Size	Tape Width	Reel (pcs)
ZK60N50S	60N50	SOP8	Reel	N/A	N/A	4000

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C = 25^{\circ}\text{C}$	I_D	50	A
	$T_C = 100^{\circ}\text{C}$		33	
Pulsed Drain Current		I_{DM}	200	A
Single Pulsed Avalanche Energy		E_{AS}	81	mJ
Power Dissipation		P_D	75	W
Thermal Resistance Junction to Case		$R_{\theta JC}$	2	$^{\circ}\text{C/W}$
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	$^{\circ}\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS

$T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Off characteristics						
Drain-source breakdown voltage	V _{(BR) DSS}	V _{GS} = 0V, I _D = 250uA	60			V
Zero gate voltage drain current	I _{DSS}	V _{DS} = 60V, V _{GS} =0V			1.0	μA
Gate-body leakage current	I _{GSS}	V _{DS} = 0V, V _{GS} =±20V			±100	nA
On characteristics ④						
Gate-threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	1.0	1.6	2.5	V
Static drain-source on-sate resistance	R _{DS(on)}	V _{GS} =10V, I _D =30A		12	15	mΩ
		V _{GS} =4.5V, I _D =20A		16	21	mΩ
Dynamic characteristics ④ ⑤						
Input capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V f =1MHz		2030		pF
Output capacitance	C _{oss}			130		
Reverse transfer capacitance	C _{rss}			115		
Switching characteristics ④ ⑤						
Total gate charge	Q _g	V _{GS} =0 to 10V V _{DS} =30V, I _D =30A		45		nC
Gate-source charge	Q _{gs}			8		
Gate-drain charge	Q _{gd}			11		
Turn-on delay time	t _{d(on)}	V _{DS} =30V, I _D =30A V _{GS} =10V, R _{GEN} =1.8Ω		11		ns
Turn-on rise time	t _r			79		
Turn-off delay time	t _{d(off)}			33		
Turn-off fall time	t _f			107		
Drain-Source Diode Characteristics						
Drain-source diode forward voltage	V _{SD} ④	V _{GS} =0V, I _S =30A			1.2	V
Continuous drain-source diode forward current	I _S ①	T _C =25℃			50	A
Pulsed drain-source diode forward current	I _{SM}				200	
Reverse recovery time	t _{rr}	di/dt = 100A/μs, I _F = 20A		14		ns
Reverse recovery charge	Q _{rr}			10		nC

Notes:

- 1.Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. EAS condition : $T_J = 25^\circ\text{C}, V_{DD} = 30V, V_G = 10V, L = 0.5mH, R_g = 25\Omega, I_{AS} = 18A$
- 3.Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

Figure1: Output Characteristics

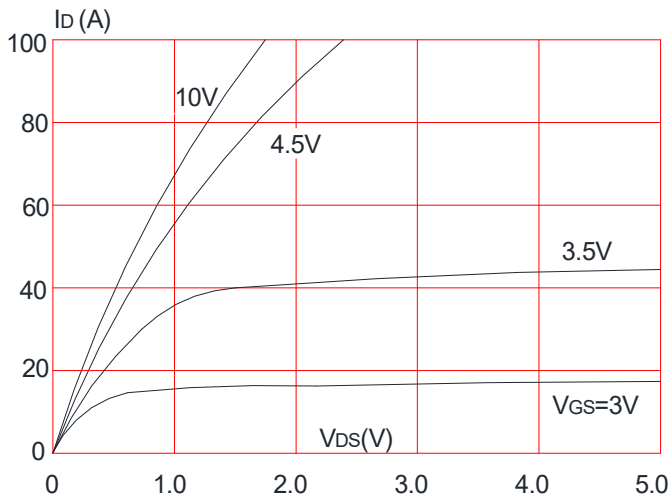


Figure 2: Typical Transfer Characteristics

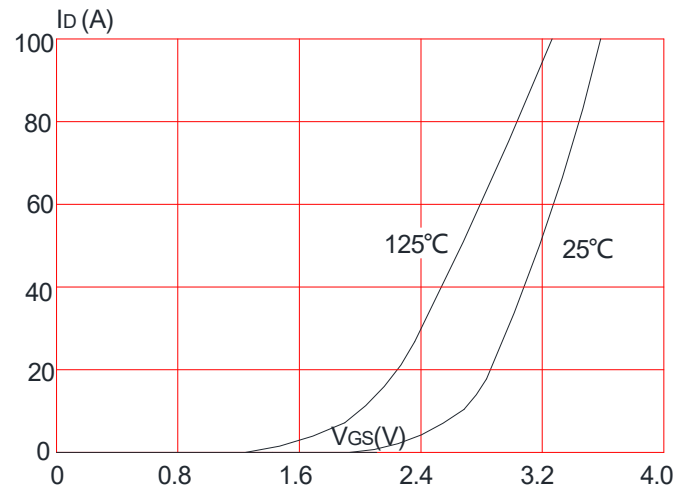


Figure 3: On-resistance vs. Drain Current

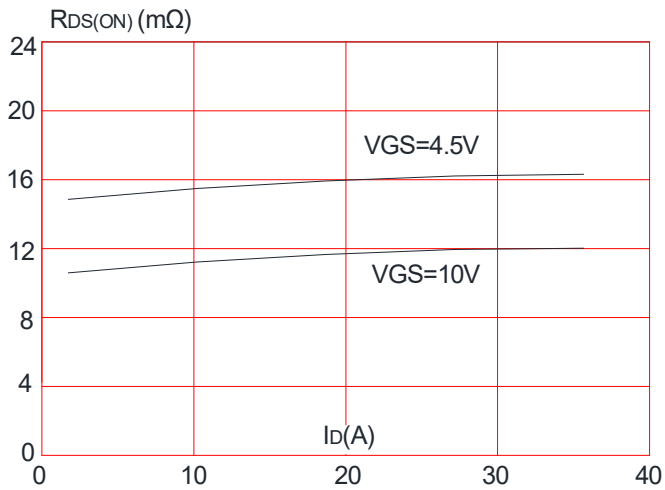


Figure 4: Body Diode Characteristics

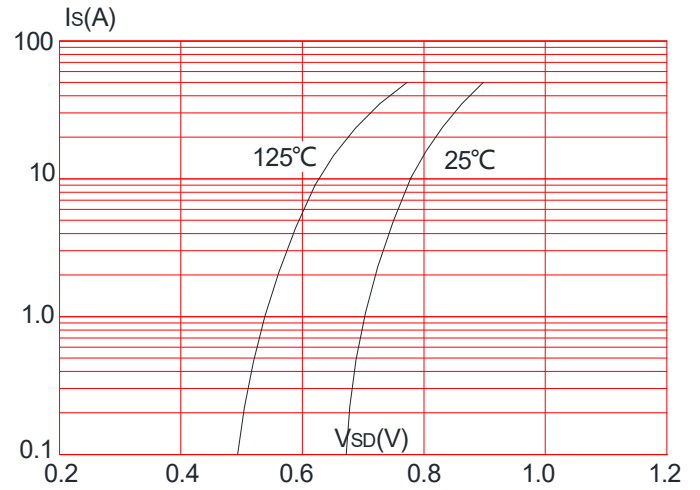


Figure 5: Gate Charge Characteristics

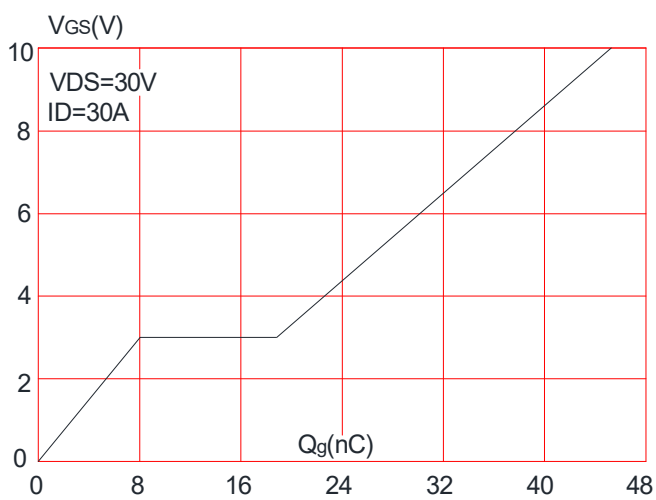
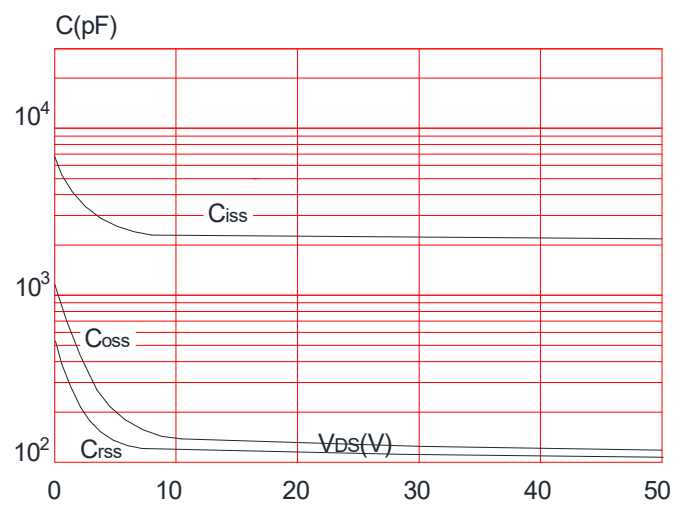


Figure 6: Capacitance Characteristics



Typical Performance Characteristics

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

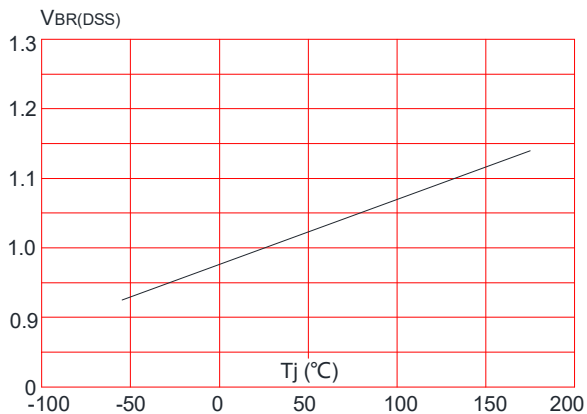


Figure 8: Normalized on Resistance vs. Junction Temperature

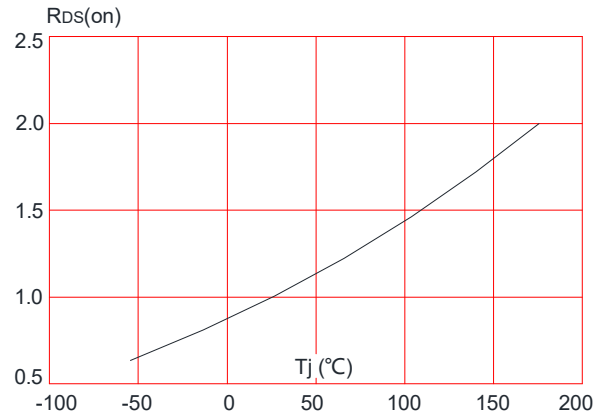


Figure 9: Maximum Safe Operating Area

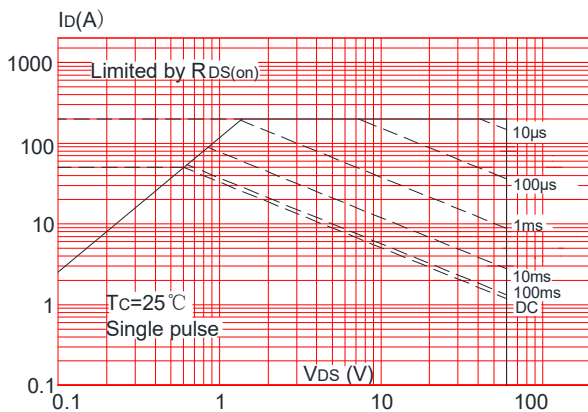


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

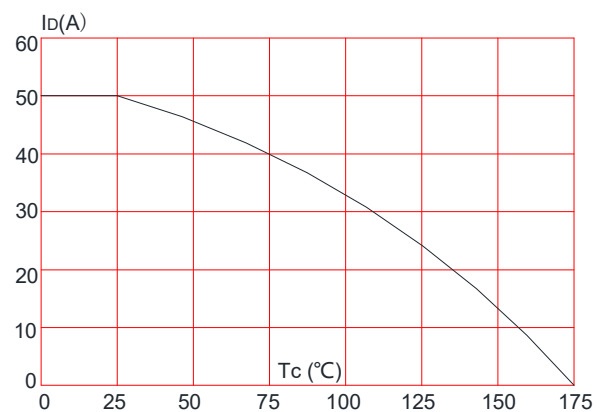
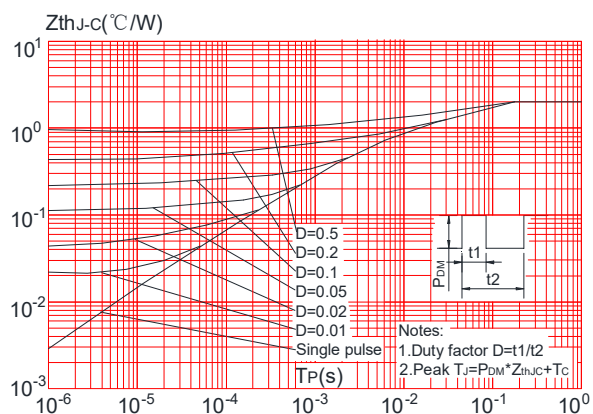


Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



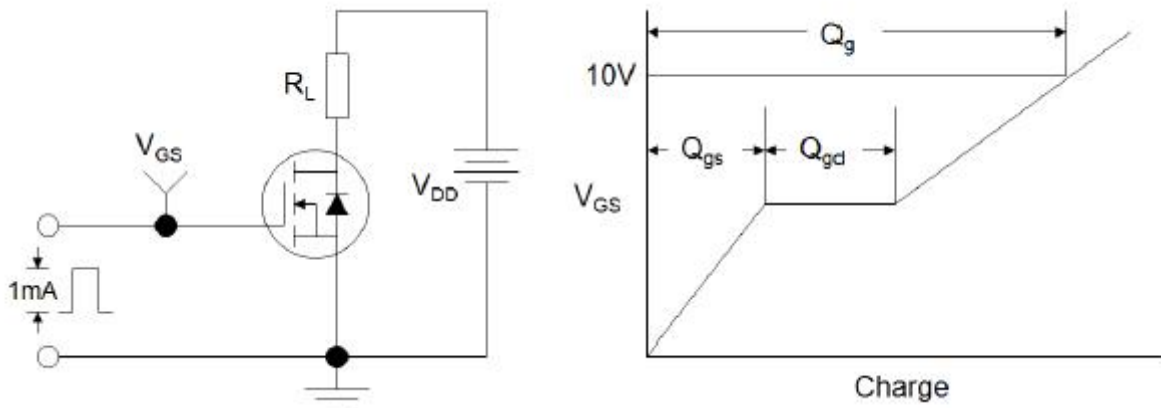


Figure1:Gate Charge Test Circuit & Waveform

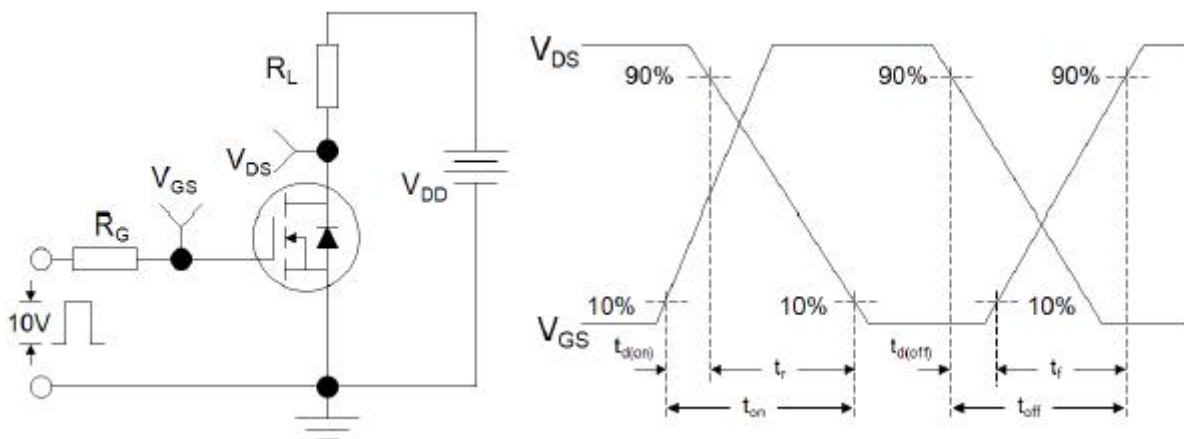
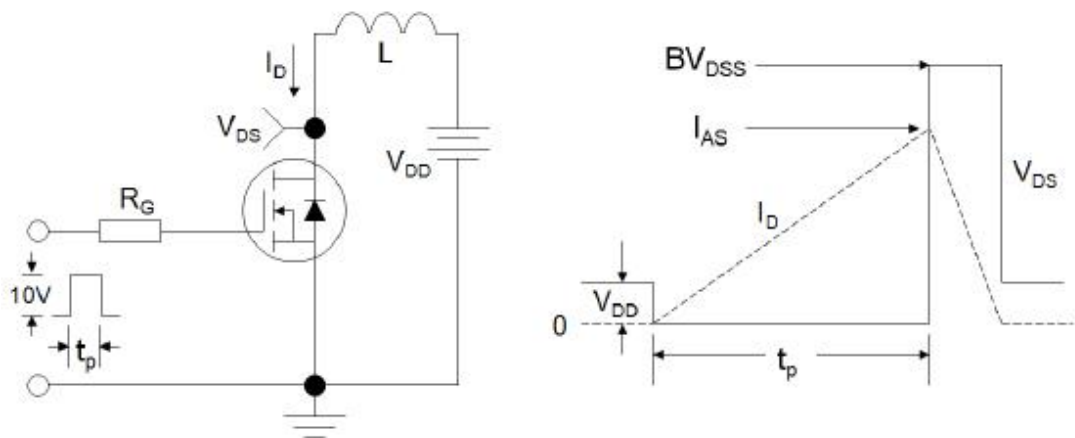
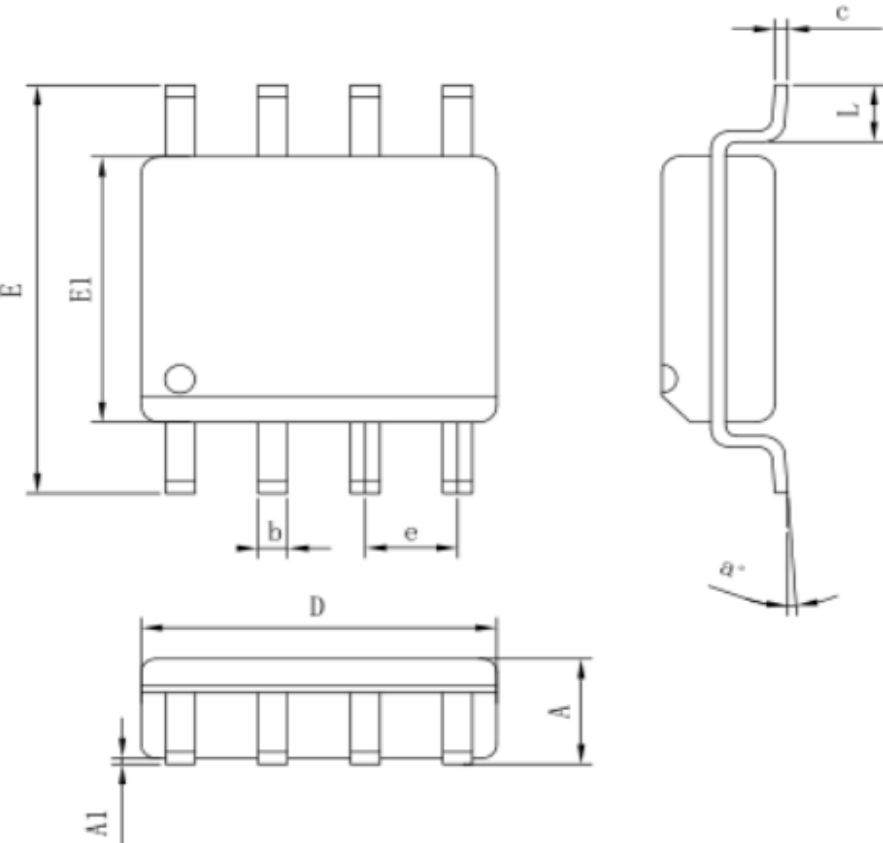


Figure 2: Resistive Switching Test Circuit & Waveforms





SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	--	--	1.75
A1	0.10	--	0.23
b	0.35	--	0.48
c	0.19	--	0.25
D	4.70	4.90	5.00
E	5.80	6.00	6.20
E1	3.70	3.90	4.10
e	1.27BSC		
L	0.50	--	0.80
α°	0°	--	8°